

## SANYO Semiconductors DATA SHEET

PNP / NPN Epitaxial Planar Silicon Transistors

# 2SA1209 / 2SC2911 — 160V / 140mA High-Voltage Switching and AF 100W Predriver Applications

#### **Features**

- · Adoption of FBET process.
- · High breakdown voltage.
- Good linearity of hFE and small Cob.
- · Fast switching time.

Specifications ( ): 2SA1209

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)180	V
Collector-to-Emitter Voltage	VCEO		(-)160	V
Emitter-to-Base Voltage	VEBO		(-)5.0	V
Collector Current	IC		(-)140	mA
Collector Current (Pulse)	ICP		(-)200	mA
Collector Dissipation	PC		1.0	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

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#### Electrical Characteristics at Ta=25°C

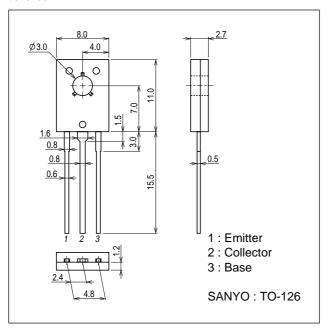
Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	VCB=(-)80V, IE=0A			(-)0.1	μА
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0A			(-)0.1	μΑ
DC Current Gain	hFE	VCE=(-)5V, IC=(-)10mA	100*		400*	
Gain-Bandwidth Product	fT	VCE=(-)10V, IC=(-)10mA		150		MHz
Output Capacitance	Cob	V <sub>CB</sub> =(-)10V, f=1MHz		(4.0)3.0		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=(-)50mA, IB=(-)5mA		(-0.14)0.07	(-0.4)0.3	V
Turn-On Time	ton	See specified Test Circuit.		0.1		μS
Storage Time	tstg	See specified Test Circuit.		1.5		μS
Fall Time	tf	See specified Test Circuit.		0.1		μs

<sup>\*:</sup> The 2SA1209/2SC2911 are classified by 10mA hFE as follows:

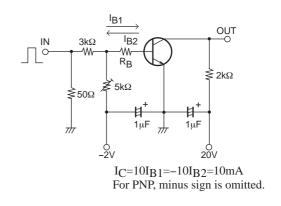
Rank	R	S	Т	
$h_{ ext{FE}}$	100 to 200	140 to 280	200 to 400	

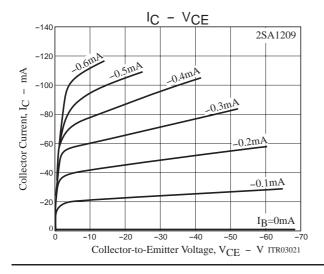
#### **Package Dimensions**

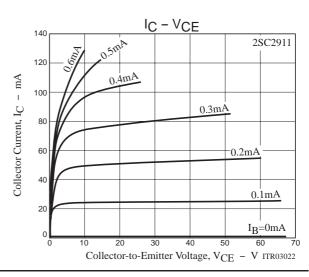
unit : mm (typ) 7515-002

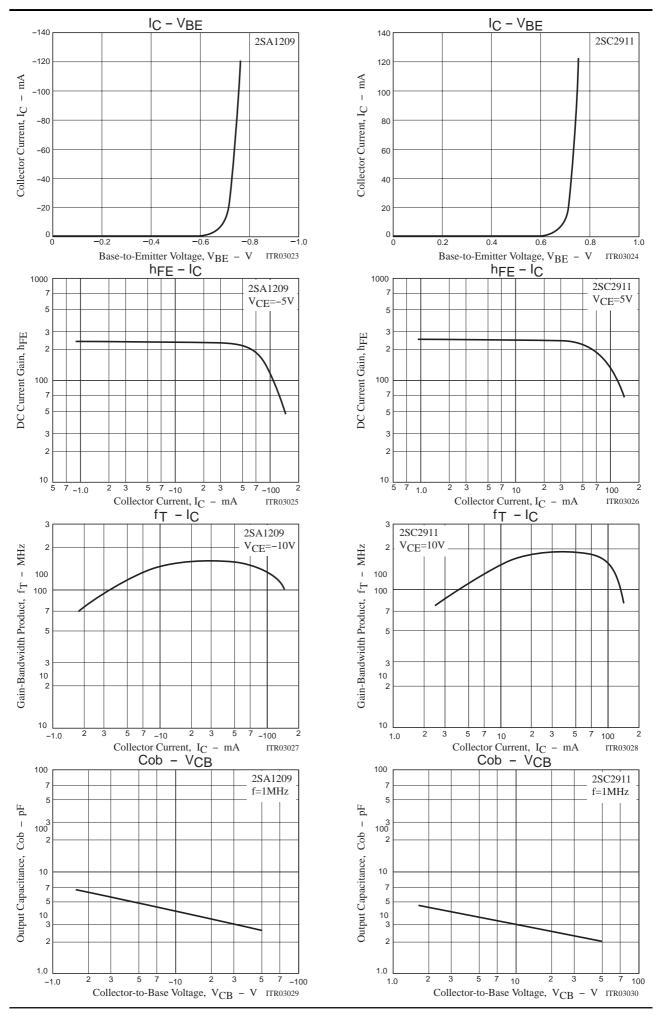


### **Switching Time Test Circuit**

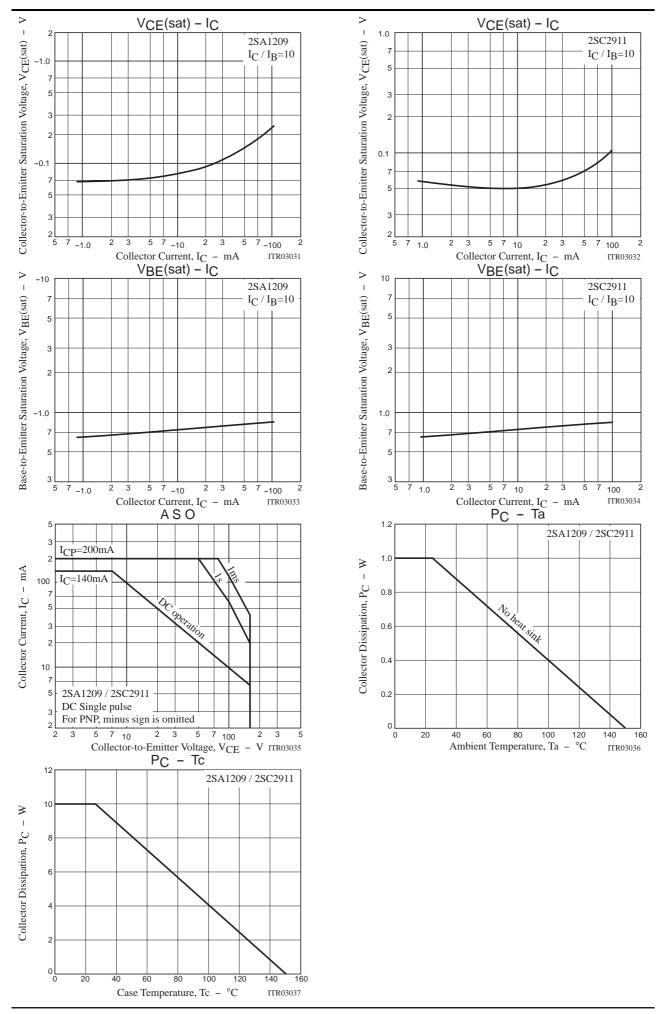








#### 2SA1209 / 2SC2911



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